

Final datasheet
CoolSiC™ 1200 V SiC MOSFET G2 : Silicon Carbide MOSFET

Features

- $V_{DS} = 1200\text{ V}$ at $T_{vj} = 25^{\circ}\text{C}$
- $I_{DC} = 36\text{ A}$ at $T_C = 100^{\circ}\text{C}$
- $R_{DS(on)} = 39.6\text{ m}\Omega$ at $V_{GS} = 18\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$
- Very low switching losses
- Overload operation up to $T_{vj} = 200^{\circ}\text{C}$
- Short circuit withstand time $2\text{ }\mu\text{s}$
- Benchmark gate threshold voltage, $V_{GS(th)} = 4.2\text{ V}$
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- Suitable Infineon gate drivers can be found under <https://www.infineon.com/gdfinder>

Potential applications

- EV Charging
- Online UPS / Industrial UPS
- String inverter
- General purpose drives (GPD)

Product validation

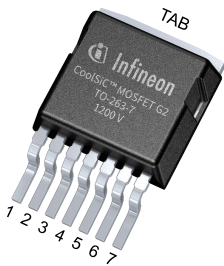
- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Description

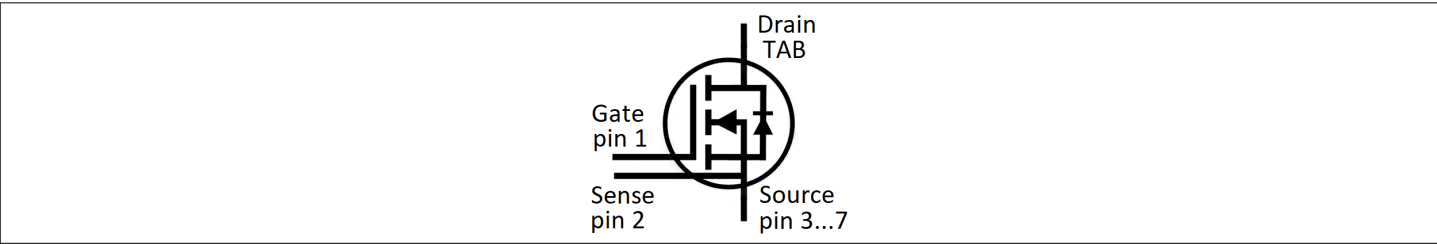
Pin definition:

- Pin 1 - Gate
- Pin 2 - Kelvin sense contact
- Pin 3...7 - Source
- Tab - Drain

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction (only for 4pin, TO263-7L)



- Halogen-free
- Green
- Lead-free
- RoHS



Type	Package	Marking
IMBG120R040M2H	PG-TO263-7-U01	12M2H040



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1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	Reflow soldering (MSL1 according to JEDEC J-STD-020)			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.46	0.6	K/W

2 MOSFET

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25\text{ °C}$		1200	V
Continuous DC drain current for $R_{th(j-c, max)}$, limited by $T_{vj(max)}$	I_{DDC}	$V_{GS} = 18\text{ V}$	$T_c = 25\text{ °C}$	52	A
			$T_c = 100\text{ °C}$	36	
Peak drain current, t_p limited by $T_{vj(max)}$ ¹⁾	I_{DM}	$V_{GS} = 18\text{ V}$		180	A
Gate-source voltage, max. transient voltage	V_{GS}	$t_p \leq 0.5\text{ }\mu\text{s}$, $D < 0.01$		-10...25	V
Gate-source voltage, max. static voltage ²⁾	V_{GS}			-7...23	V
Avalanche energy, single pulse	E_{AS}	$I_D = 17.5\text{ A}$, $V_{DD} = 50\text{ V}$, $L = 1.4\text{ mH}$, $T_{vj(start)} = 25\text{ °C}$		220	mJ
Avalanche energy, repetitive	E_{AR}	$I_D = 17.5\text{ A}$, $V_{DD} = 50\text{ V}$, $L = 7.2\text{ }\mu\text{H}$, $T_{vj(start)} = 25\text{ °C}$		1.1	mJ
Short-circuit withstand time	t_{SC}	$V_{DD} \leq 800\text{ V}$, $V_{DS, peak} < 1200\text{ V}$, $V_{GS(on)} = 15\text{ V}$, $T_{vj(start)} = 25\text{ °C}$		2	μs
Power dissipation, limited by $T_{vj(max)}$	P_{tot}		$T_c = 25\text{ °C}$	250	W
			$T_c = 100\text{ °C}$	125	

1) verified by design.

2) The maximum gate-source voltage in the application design should be in accordance to IPC-9592B.

Table 3 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 17.5 \text{ A}$		$T_{vj} = 25 \text{ °C}$, $V_{GS(on)} = 18 \text{ V}$	39.6	mΩ
				$T_{vj} = 150 \text{ °C}$, $V_{GS(on)} = 18 \text{ V}$	81	
				$T_{vj} = 175 \text{ °C}$, $V_{GS(on)} = 18 \text{ V}$	94	
				$T_{vj} = 25 \text{ °C}$, $V_{GS(on)} = 15 \text{ V}$	49.4	
Gate-source threshold voltage	$V_{GS(th)}$	$I_D = 5.5 \text{ mA}$, $V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20 \text{ V}$)		$T_{vj} = 25 \text{ °C}$	3.5	V
				$T_{vj} = 175 \text{ °C}$	4.2	
Zero gate-voltage drain current	I_{DSS}	$V_{DS} = 1200 \text{ V}$, $V_{GS} = 0 \text{ V}$		$T_{vj} = 25 \text{ °C}$		μA
				$T_{vj} = 175 \text{ °C}$	2.6	
Gate leakage current	I_{GSS}	$V_{DS} = 0 \text{ V}$		$V_{GS} = 23 \text{ V}$		nA
				$V_{GS} = -10 \text{ V}$	120	
Forward transconductance	g_{fs}	$I_D = 17.5 \text{ A}$, $V_{DS} = 20 \text{ V}$			11.8	S
Internal gate resistance	$R_{G,int}$	$f = 1 \text{ MHz}$, $V_{AC} = 25 \text{ mV}$			6.5	Ω
Input capacitance	C_{iss}	$V_{DS} = 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 100 \text{ kHz}$, $V_{AC} = 25 \text{ mV}$			1310	pF
Output capacitance	C_{oss}	$V_{DS} = 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 100 \text{ kHz}$, $V_{AC} = 25 \text{ mV}$			55	pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 100 \text{ kHz}$, $V_{AC} = 25 \text{ mV}$			4.7	pF
C_{oss} stored energy	E_{oss}	Calculated based on $C_{oss} = f(V_{DD})$			23	μJ
Output charge	Q_{oss}	Calculated based on $C_{oss} = f(V_{DD})$			85.2	nC
Effective output capacitance, energy related	$C_{o(er)}$	$V_{DS} = 0...800 \text{ V}$, $V_{GS} = 0 \text{ V}$, Calculated based on E_{oss}			71.9	pF
Effective output capacitance, time related	$C_{o(tr)}$	$I_D = \text{constant}$, $V_{DS} = 0...800 \text{ V}$, $V_{GS} = 0 \text{ V}$, Calculated based on Q_{oss}			106.5	pF
Total gate charge	Q_G	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, turn-on pulse			39	nC

(table continues...)

Table 4 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, turn-on pulse		8.5		nC
Gate-drain charge	Q_{GD}	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, turn-on pulse		10.4		nC
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 15 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	3		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$	3.2		
Rise time	t_r	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 15 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	14.7		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$	14.5		
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 15 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	6.4		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$	11.1		
Fall time	t_f	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 15 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	4		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$	4.7		
Turn-on energy	E_{on}	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 15 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	113		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	222		
Turn-off energy	E_{off}	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 15 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	24		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	35		
Total switching energy ¹⁾	E_{tot}	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 15 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	187		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	397		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on energy at -5 V	E_{on}	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = -5/18 \text{ V}$, $R_{G,ext} = 2.3 \text{ } \Omega$, $L_\sigma = 15 \text{ nH}$, diode: body diode at $V_{GS} = -5 \text{ V}$	$T_{vj} = 25 \text{ } ^\circ\text{C}$	129		μJ
			$T_{vj} = 175 \text{ } ^\circ\text{C}$	277		
Turn-off energy at -5 V	E_{off}	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = -5/18 \text{ V}$, $R_{G,ext} = 2.3 \text{ } \Omega$, $L_\sigma = 15 \text{ nH}$, diode: body diode at $V_{GS} = -5 \text{ V}$	$T_{vj} = 25 \text{ } ^\circ\text{C}$	23		μJ
			$T_{vj} = 175 \text{ } ^\circ\text{C}$	23		
Total switching energy at -5 V ¹⁾	E_{tot}	$V_{DD} = 800 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{GS} = -5/18 \text{ V}$, $R_{G,ext} = 2.3 \text{ } \Omega$, $L_\sigma = 15 \text{ nH}$, diode: body diode at $V_{GS} = -5 \text{ V}$	$T_{vj} = 25 \text{ } ^\circ\text{C}$	205		μJ
			$T_{vj} = 175 \text{ } ^\circ\text{C}$	484		
Virtual junction temperature	T_{vj}		-55		175	$^\circ\text{C}$
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h ²⁾			200	$^\circ\text{C}$

1) including E_{fr}

2) up to 5000 cycles. Maximum ΔT limited to 100 K.

Note: The chip technology was characterized up to 200 kV/ μs . The measured dV/dt was limited by measurement test setup and package.

Characteristics at $T_{vj} = 25^\circ\text{C}$, unless otherwise specified.

3 Body diode (MOSFET)

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25 \text{ } ^\circ\text{C}$		1200	V
Continuous reverse drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{SDC}	$V_{GS} = 0 \text{ V}$	$T_c = 25 \text{ } ^\circ\text{C}$	43	A
			$T_c = 100 \text{ } ^\circ\text{C}$	24.5	
Peak reverse drain current, t_p limited by $T_{vj(max)}$	I_{SM}	$V_{GS} = 0 \text{ V}$		111	A

Table 6 Characteristic values

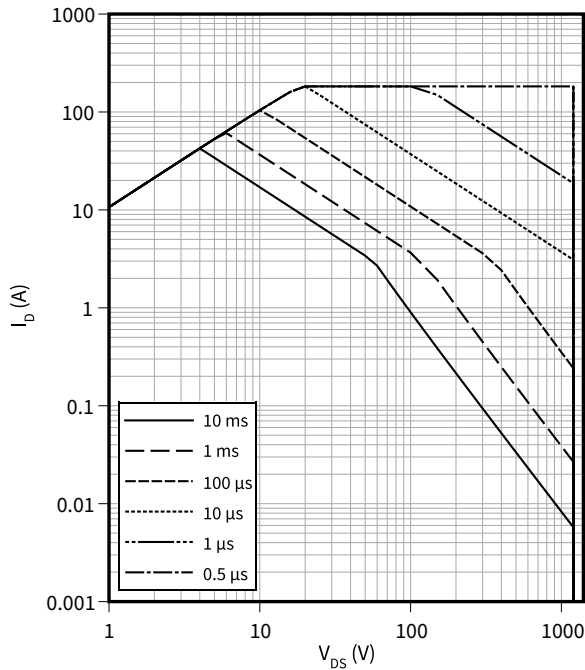
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Drain-source reverse voltage	V_{SD}	$I_{SD} = 17.5 \text{ A}$, $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$	4.2	5.5	V
			$T_{vj} = 100 \text{ °C}$	4.11		
			$T_{vj} = 175 \text{ °C}$	4.05		
MOSFET forward recovery charge	Q_{fr}	$V_{DD} = 800 \text{ V}$, $I_{SD} = 17.5 \text{ A}$, $V_{GS} = 0 \text{ V}$, $R_{G,ext} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ °C}$	0.57		μC
			$T_{vj} = 175 \text{ °C}$	0.73		
MOSFET peak forward recovery current	I_{frm}	$V_{DD} = 800 \text{ V}$, $I_{SD} = 17.5 \text{ A}$, $V_{GS} = 0 \text{ V}$, $R_{G,ext} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ °C}$	34		A
			$T_{vj} = 175 \text{ °C}$	47		
MOSFET forward recovery energy	E_{fr}	$V_{DD} = 800 \text{ V}$, $I_{SD} = 17.5 \text{ A}$, $V_{GS} = 0 \text{ V}$, $R_{G,ext} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ °C}$	50		μJ
			$T_{vj} = 175 \text{ °C}$	140		
MOSFET forward recovery energy at -5 V	E_{fr}	$V_{DD} = 800 \text{ V}$, $I_{SD} = 17.5 \text{ A}$, $V_{GS} = -5 \text{ V}$, $R_{G,ext} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ °C}$	53		μJ
			$T_{vj} = 175 \text{ °C}$	184		
Virtual junction temperature	T_{vj}		-55		175	$^{\circ}\text{C}$
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h ¹⁾			200	$^{\circ}\text{C}$

1) up to 5000 cycles. Maximum ΔT limited to 100 K.

4 Characteristics diagrams

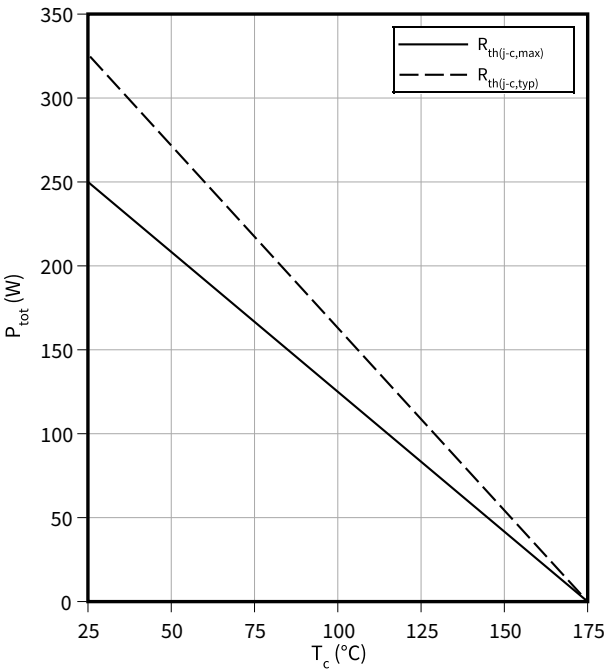
Safe operating area (SOA)

$I_D = f(V_{DS})$
 $T_{vj} \leq 175\text{ °C}, T_c = 25\text{ °C}$



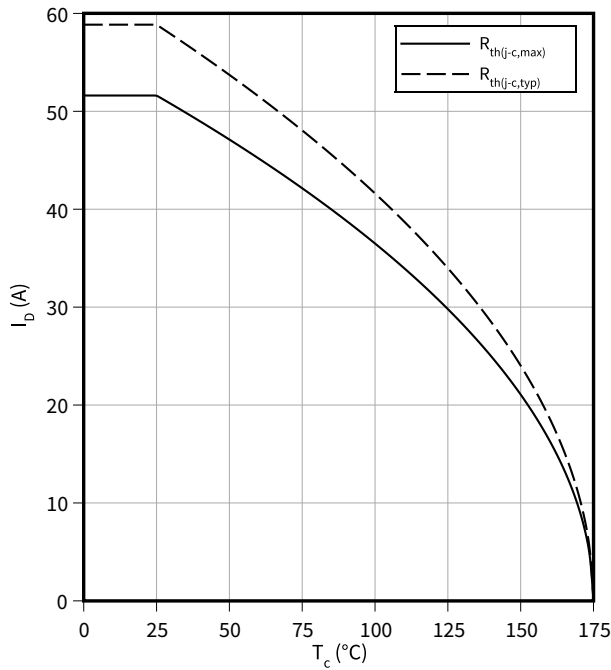
Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$



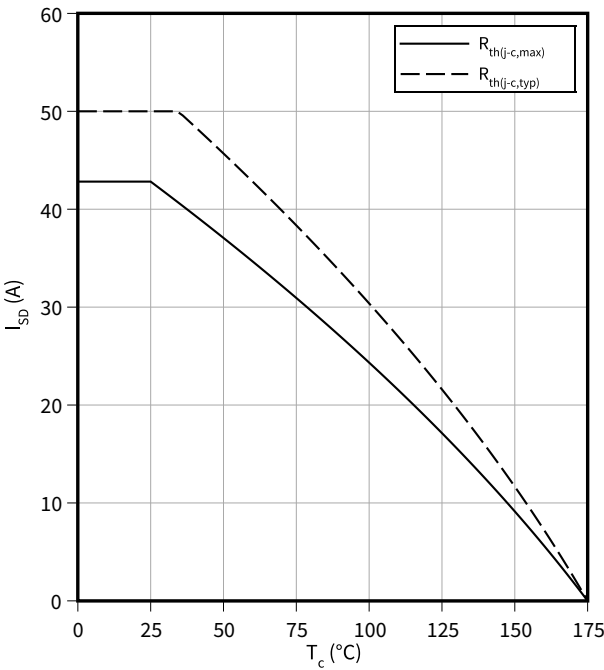
Maximum DC drain to source current as a function of case temperature limited by bond wire

$I_D = f(T_c)$



Maximum source to drain current as a function of case temperature limited by bond wire

$I_{SD} = f(T_c)$
 $V_{GS} = 0\text{ V}$

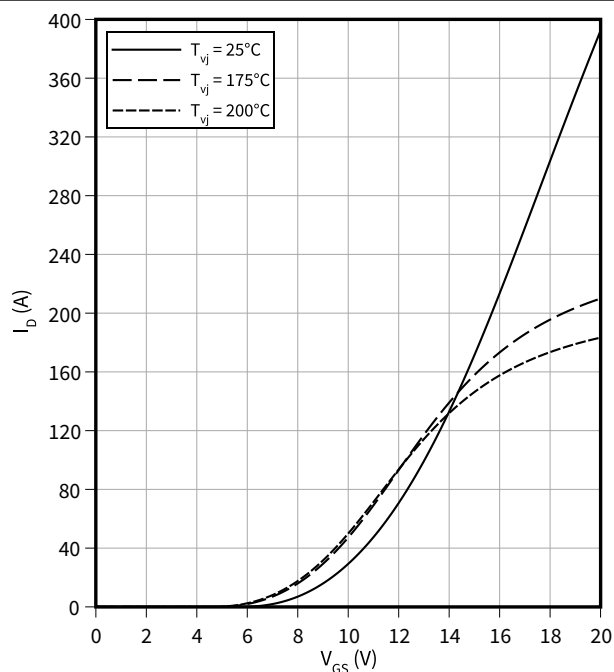


4 Characteristics diagrams

Typical transfer characteristic

$$I_D = f(V_{GS})$$

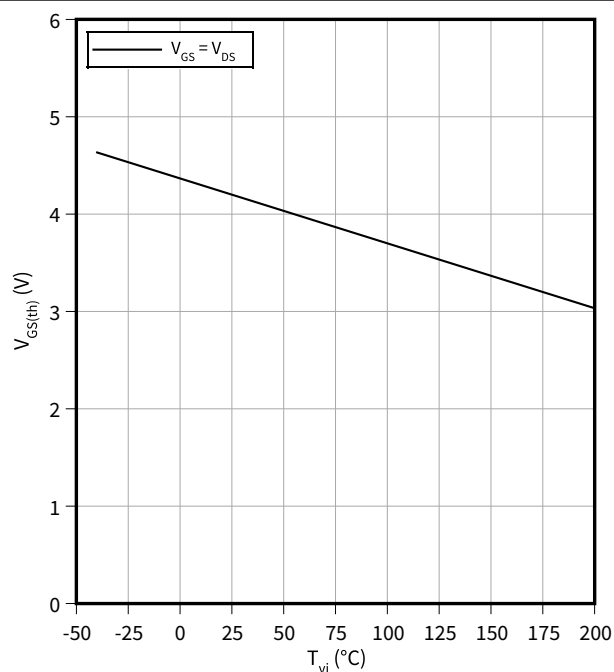
$$V_{DS} = 20 \text{ V}, t_p = 20 \mu\text{s}$$



Typical gate-source threshold voltage as a function of junction temperature

$$V_{GS(th)} = f(T_{vj})$$

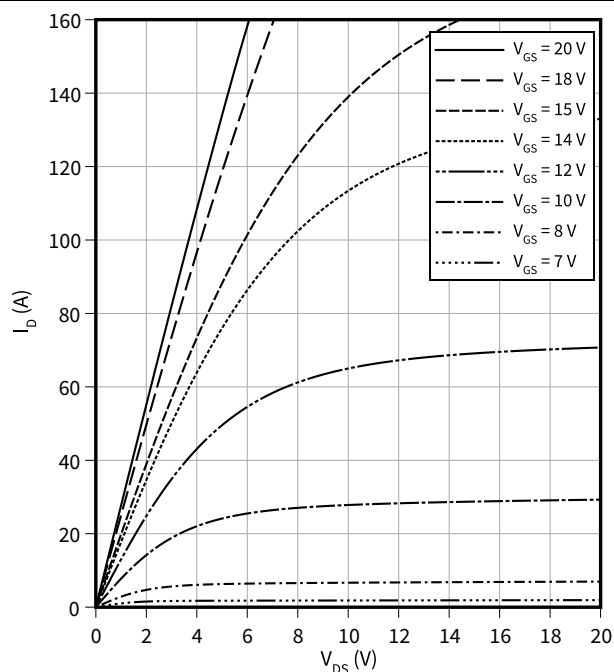
$$I_D = 5.5 \text{ mA}$$



Typical output characteristic, V_{GS} as a parameter

$$I_D = f(V_{DS})$$

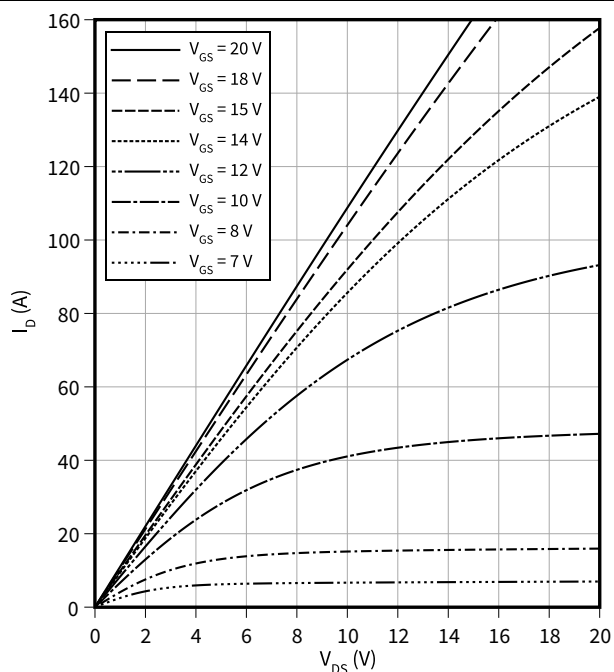
$$T_{vj} = 25 \text{ °C}, t_p = 20 \mu\text{s}$$



Typical output characteristic, V_{GS} as a parameter

$$I_D = f(V_{DS})$$

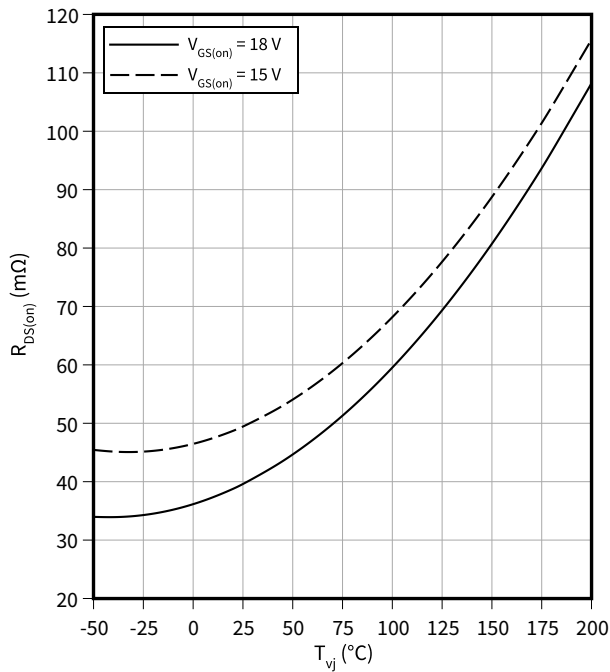
$$T_{vj} = 175 \text{ °C}, t_p = 20 \mu\text{s}$$



4 Characteristics diagrams

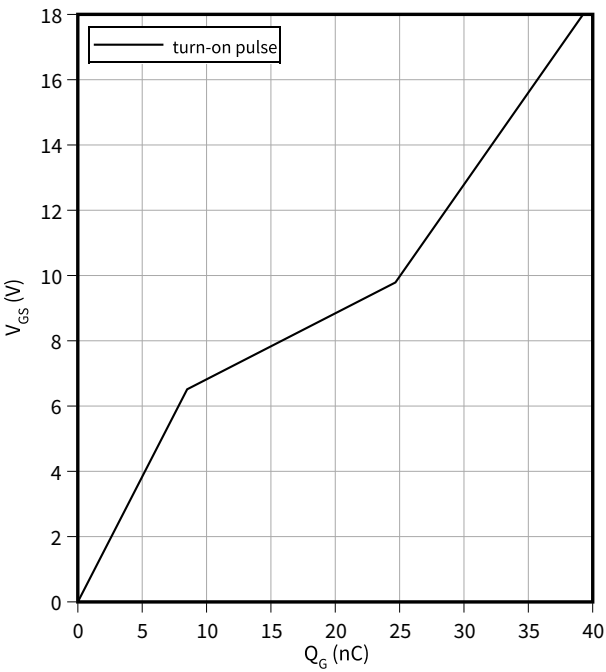
Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$
 $I_D = 17.5\text{ A}$



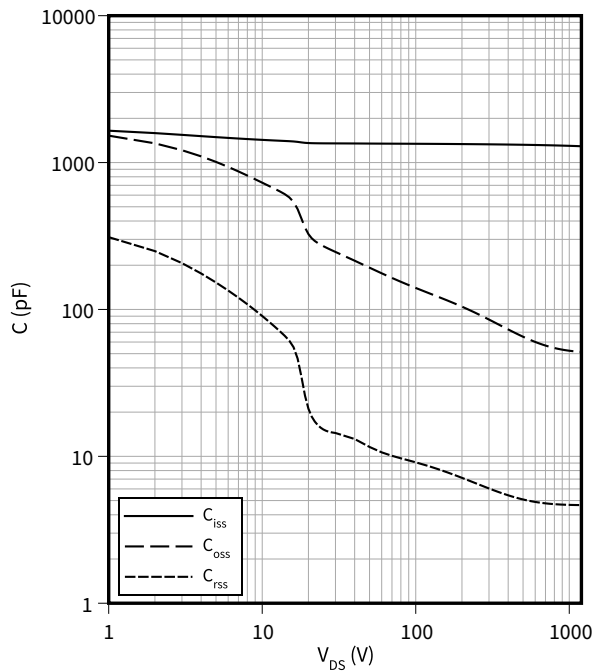
Typical gate charge

$V_{GS} = f(Q_G)$
 $I_D = 17.5\text{ A}, V_{DS} = 800\text{ V}$



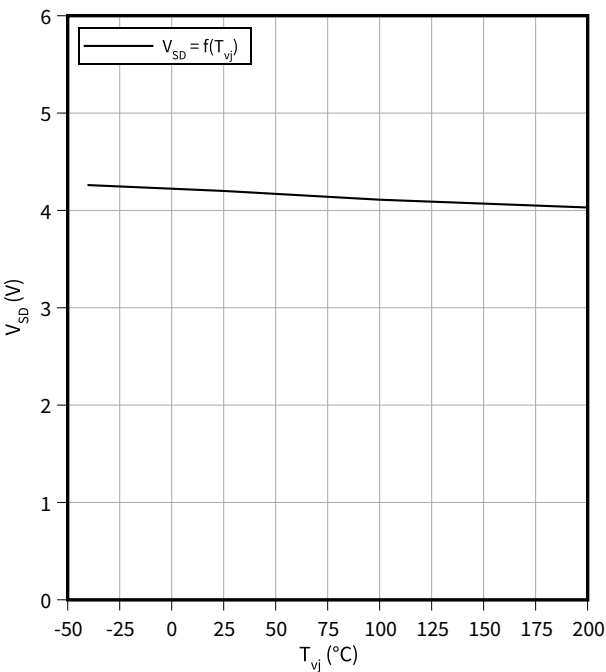
Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$
 $f = 100\text{ kHz}, V_{GS} = 0\text{ V}$



Typical reverse drain voltage as a function of junction temperature

$V_{SD} = f(T_{vj})$
 $I_{SD} = 17.5\text{ A}, V_{GS} = 0\text{ V}$

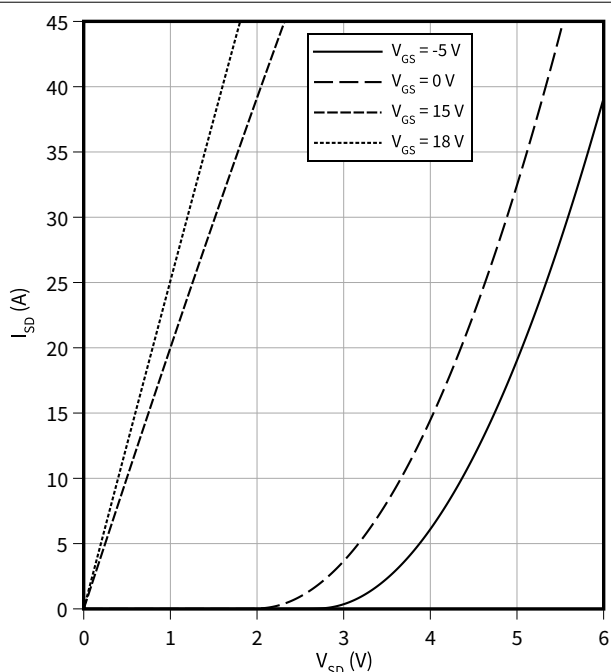


4 Characteristics diagrams

Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$$I_{SD} = f(V_{SD})$$

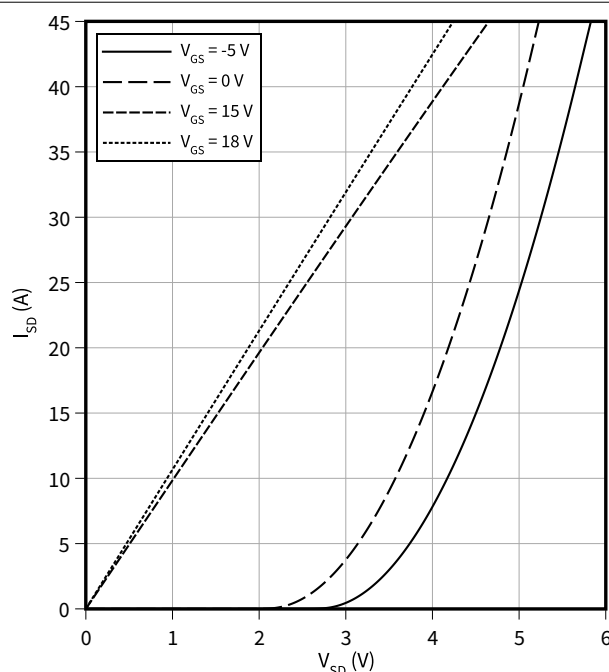
$T_{vj} = 25\text{ °C}$, $t_p = 20\text{ }\mu\text{s}$



Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$$I_{SD} = f(V_{SD})$$

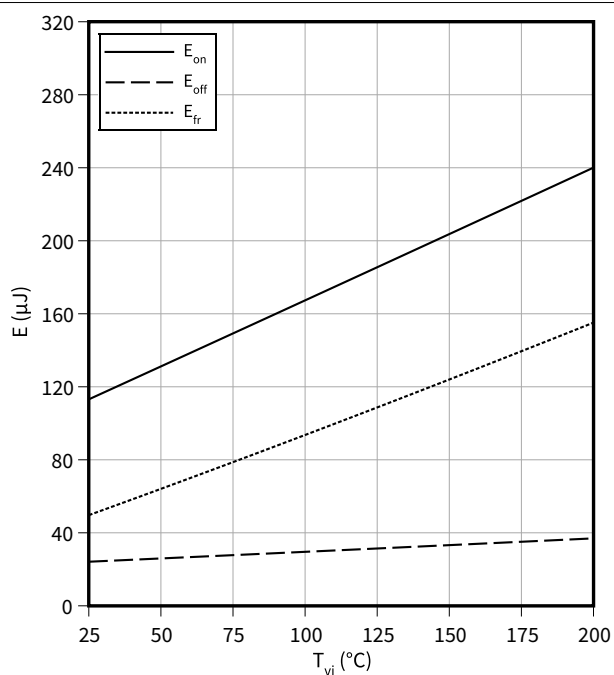
$T_{vj} = 175\text{ °C}$, $t_p = 20\text{ }\mu\text{s}$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$$E = f(T_{vj})$$

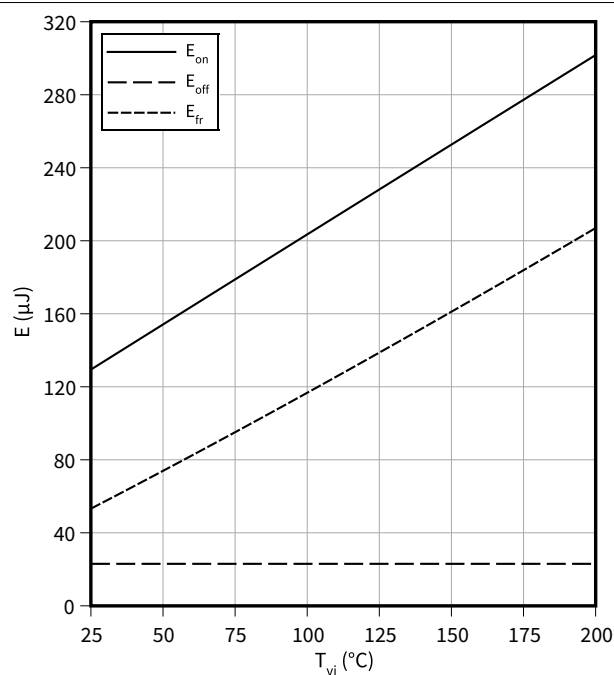
$V_{GS} = 0/18\text{ V}$, $I_D = 17.5\text{ A}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5\text{ V}$

$$E = f(T_{vj})$$

$V_{GS} = -5/18\text{ V}$, $I_D = 17.5\text{ A}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$

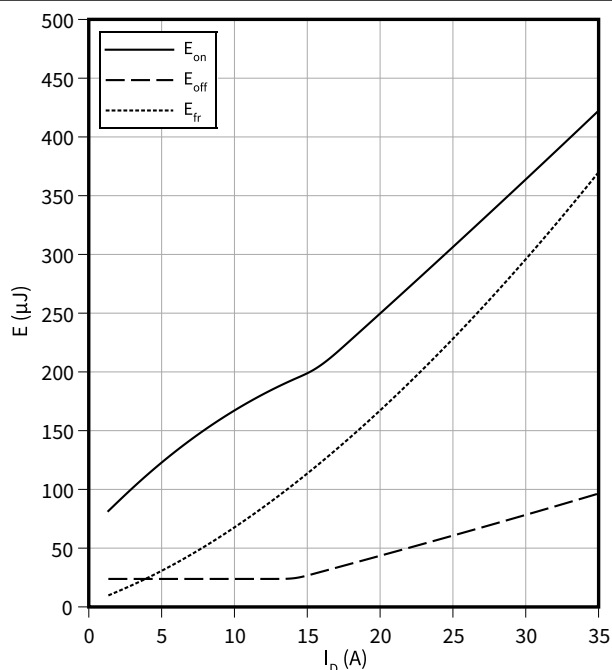


4 Characteristics diagrams

Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$E = f(I_D)$$

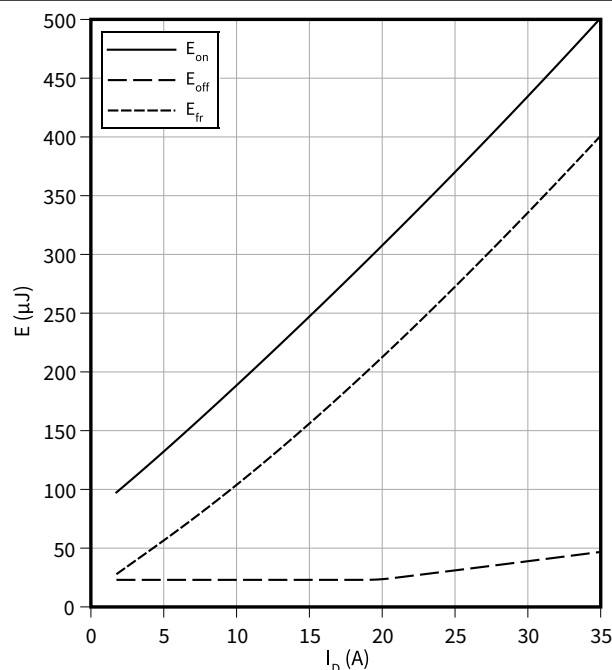
$V_{GS} = 0/18$ V, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω , $V_{DD} = 800$ V



Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5$ V

$$E = f(I_D)$$

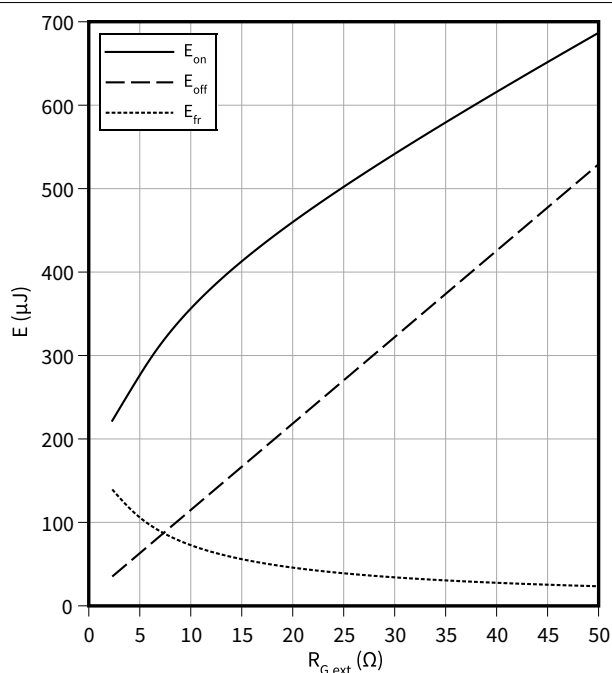
$V_{GS} = -5/18$ V, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω , $V_{DD} = 800$ V



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$E = f(R_{G,ext})$$

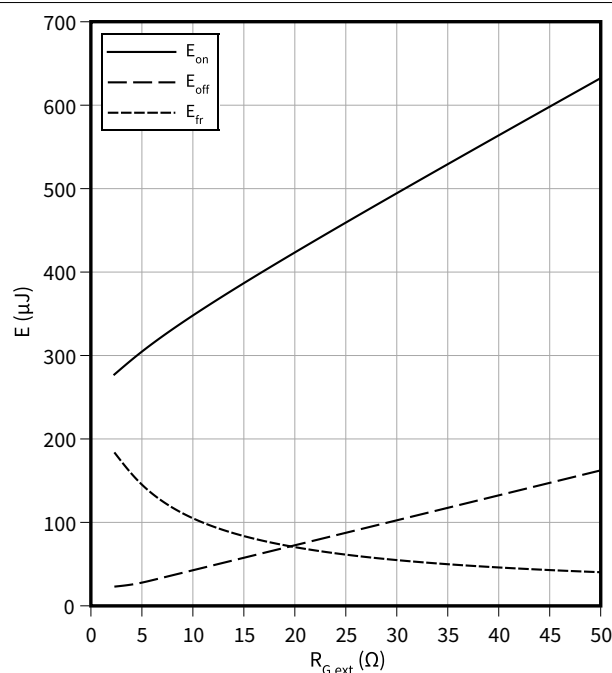
$V_{GS} = 0/18$ V, $I_D = 17.5$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5$ V

$$E = f(R_{G,ext})$$

$V_{GS} = -5/18$ V, $I_D = 17.5$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V

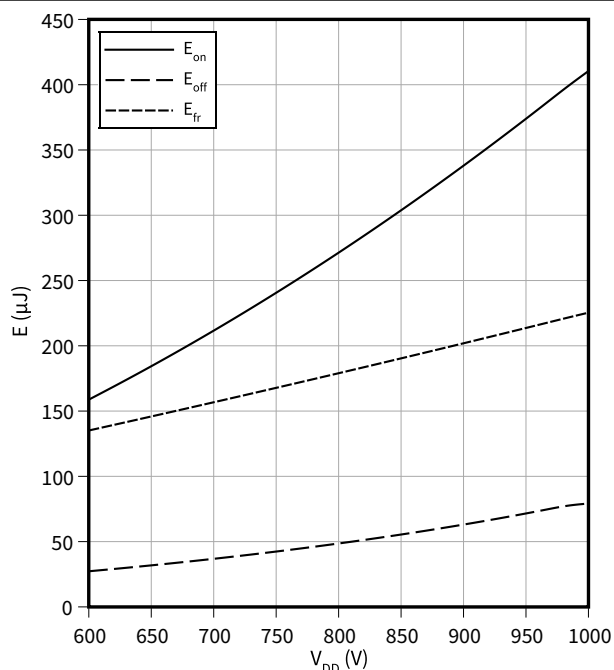


4 Characteristics diagrams

Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$E = f(V_{DD})$$

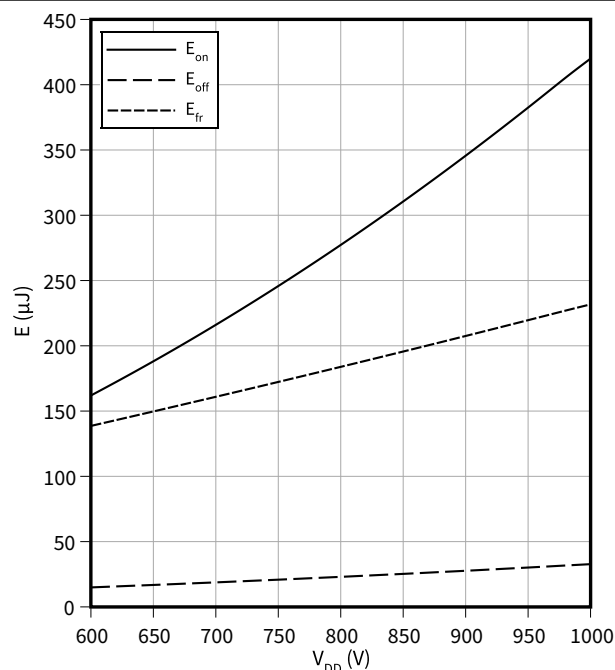
$V_{GS} = 0/18$ V, $I_D = 17.5$ A, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω



Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5$ V

$$E = f(V_{DD})$$

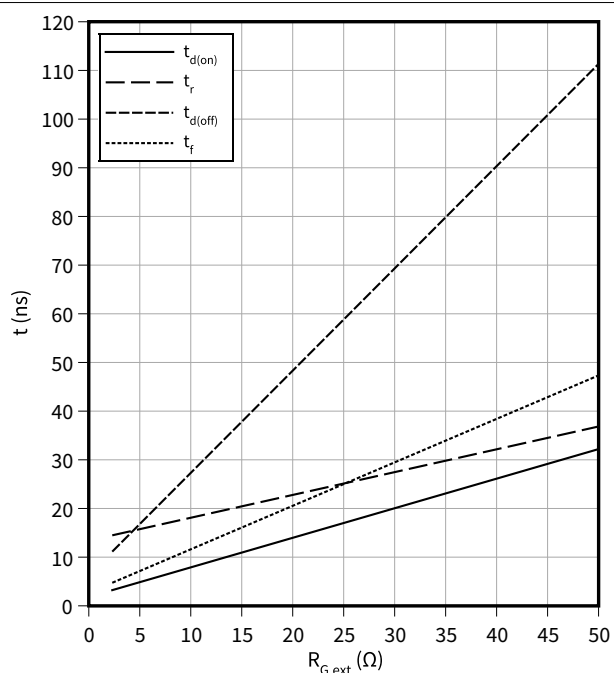
$V_{GS} = -5/18$ V, $I_D = 17.5$ A, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω



Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$t = f(R_{G,ext})$$

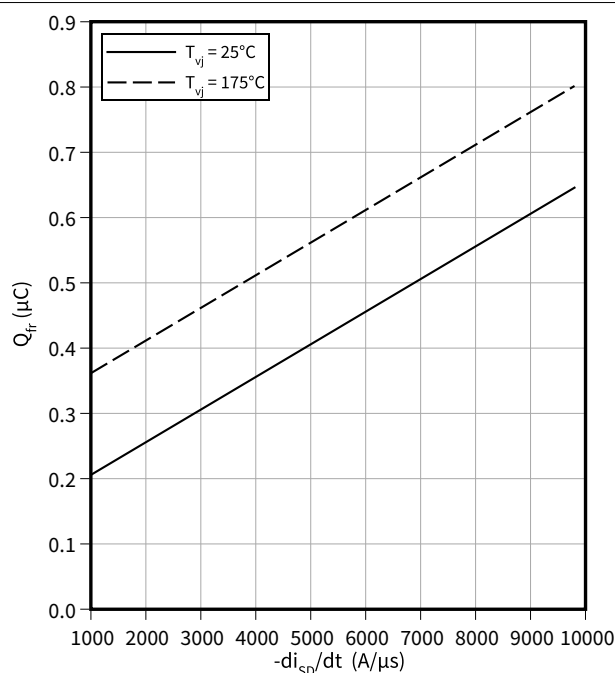
$V_{GS} = 0/18$ V, $I_D = 17.5$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V



Typical reverse recovery charge as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$Q_{fr} = f(-di_{SD}/dt)$$

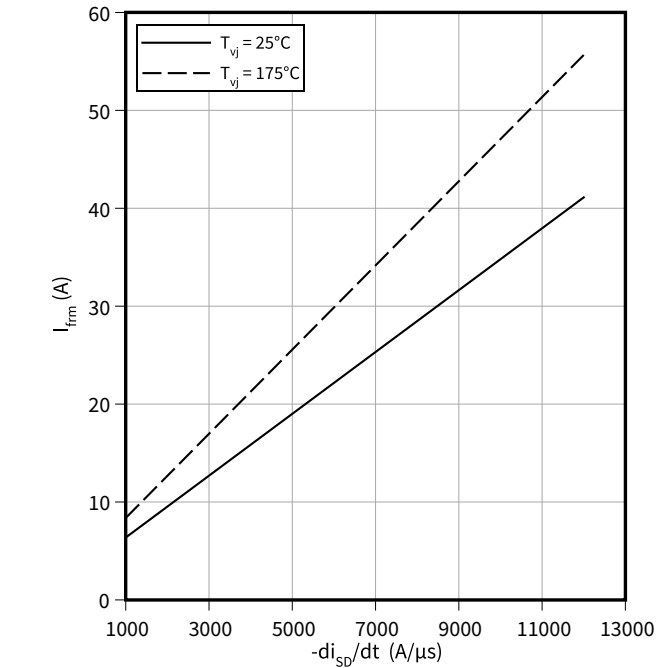
$V_{GS} = 0/18$ V, $I_{SD} = 17.5$ A, $V_{DD} = 800$ V



4 Characteristics diagrams

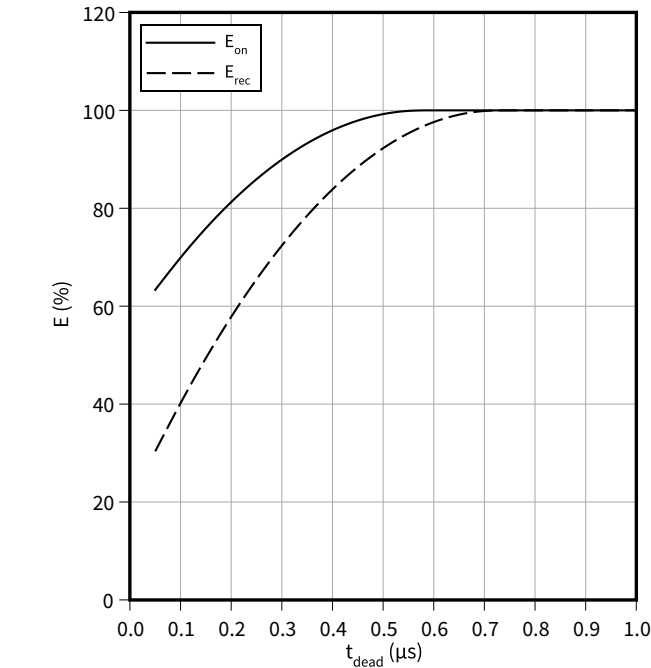
Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$I_{frm} = f(-di_{SD}/dt)$
 $V_{GS} = 0/18\text{ V}, I_{SD} = 17.5\text{ A}, V_{DD} = 800\text{ V}$



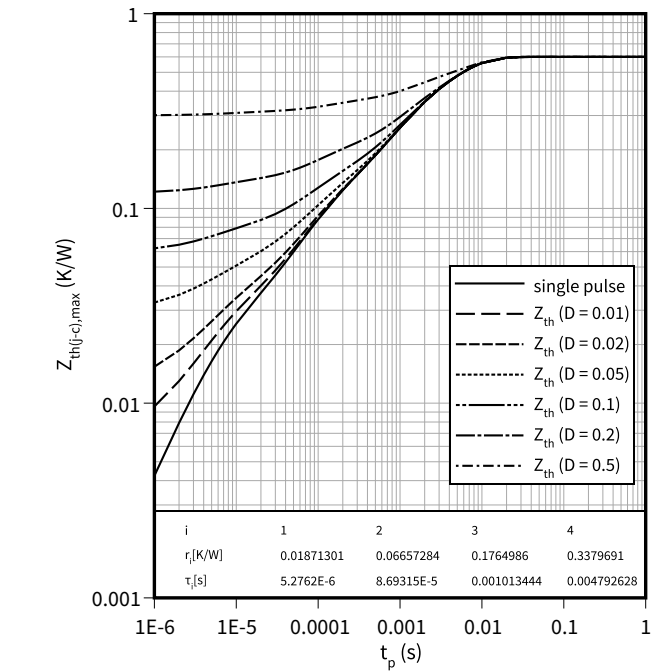
Typical switching energy as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5\text{ V}$

$E = f(t_{dead})$
 $V_{GS} = 0/18\text{ V}, I_D = 17.5\text{ A}, T_{vj} = 175\text{ °C}, R_{G,ext} = 2.3\text{ }\Omega$
 $V_{DD} = 800\text{ V}$



Max. transient thermal impedance (MOSFET/diode)

$Z_{th(j-c),max} = f(t_p)$
 $D = t_p/T$



5 Package outlines

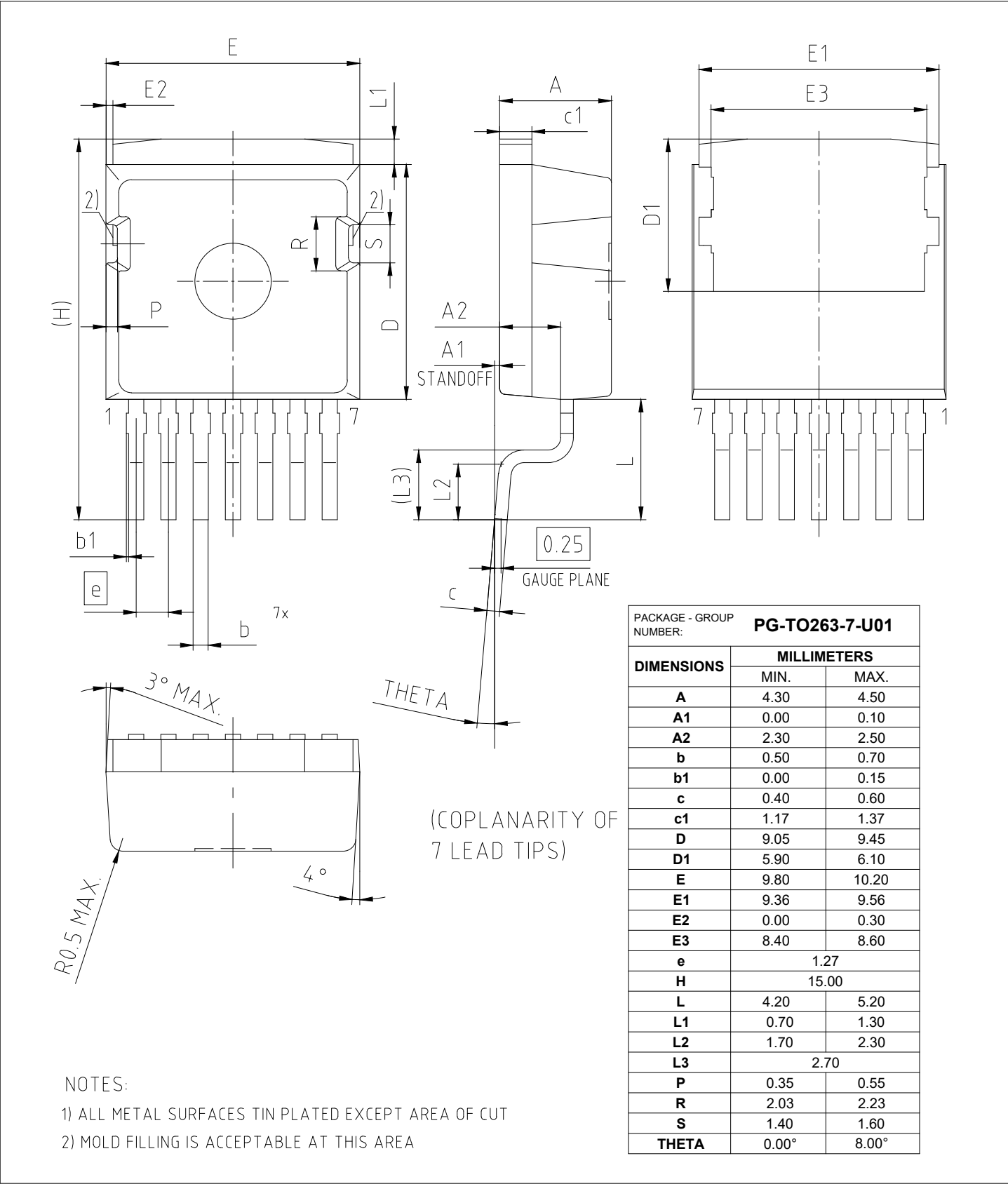


Figure 1

6 Testing conditions

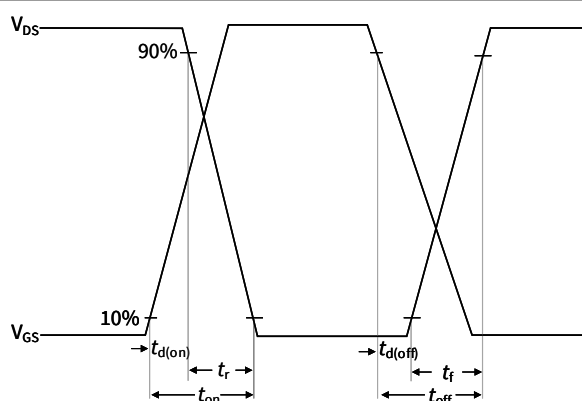


Figure A. Definition of switching times

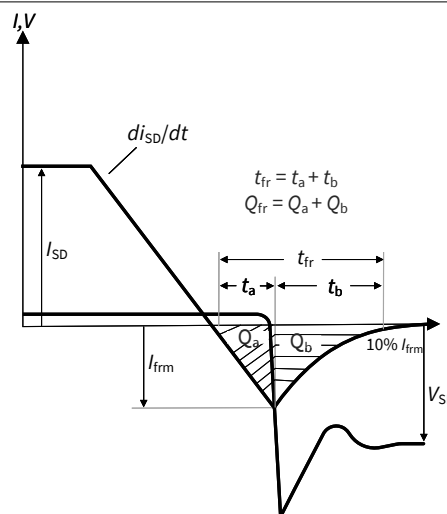


Figure B. Definition of body diode switching characteristics

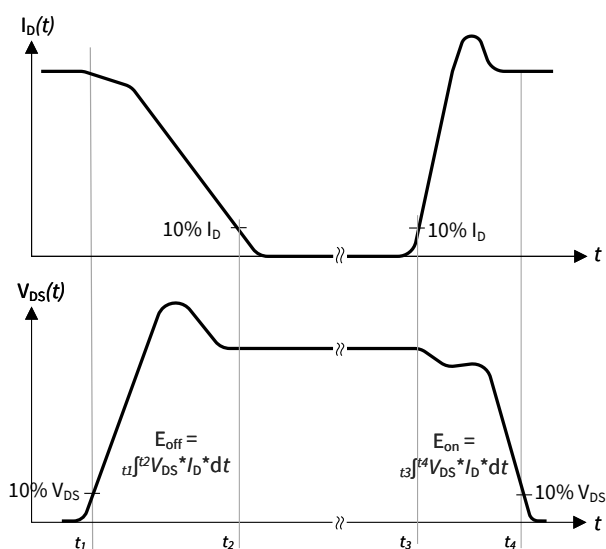


Figure C. Definition of switching losses

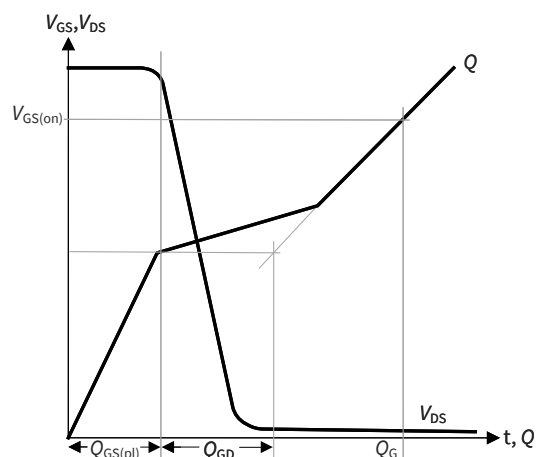


Figure D. Definition of Q_{GD}

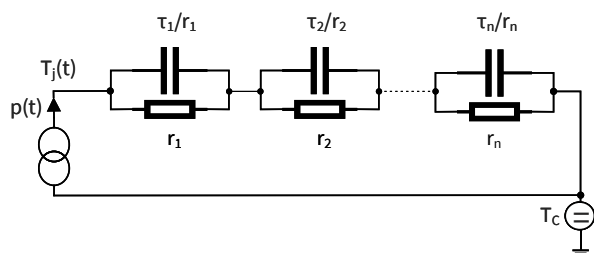


Figure E. Thermal equivalent circuit

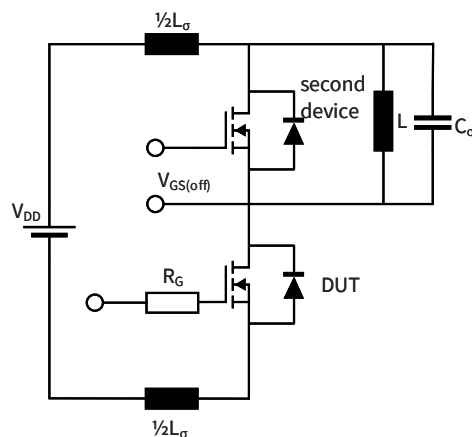


Figure F. Dynamic test circuit

Parasitic inductance L_{σ} ,
Parasitic capacitor C_{σ} ,

Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2023-08-08	Preliminary datasheet
1.00	2023-10-05	Final datasheet
1.10	2024-01-16	Negative gate voltage values updated Additional capacitance & charge values added $E = f(t_{\text{dead}})$ graph y-axis correction to percentage values Editorial changes
1.20	2024-07-02	Updated „Potential applications“ Corrected package name Corrected static and dynamic gate-source voltage Corrected unit of L to μH for “Avalanche energy, repetitive” Corrected value of g_{fs} in the Table 4 Corrected diagrams "Typical transfer characteristic" and "Max. transient thermal impedance (MOSFET/diode)" Updated Figure D. Definition of QGD
1.30	2024-11-08	Corrected diagram $I_{\text{frm}} = f(-di_{SD}/dt)$ Editorial changes
1.40	2026-01-27	Increased I_{DM} in Table 2 Corrected conditions for Q_G , $Q_{GS(pl)}$ and Q_{GD} in Table 4 Added switching information for $V_{GS} = -5/18\text{ V}$ in Table 4 and 6 and corresponding diagrams Added I_{SDC} in Table 5 Corrected test conditions and adapt values of the body diode in Table 6 Added SOA diagram on page 8 Added diagram $E = f(V_{DD}) @ V_{GS} = 0/18\text{ V}$ Added diagram $E = f(V_{DD}) @ V_{GS} = -5/18\text{ V}$ Editorial changes

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